

ABSTRACT OF THE DISCLOSURE

In a photoelectric conversion device, to suppress alteration of its properties during a long time use, lower decrease of S/N ratio due to a dark current 5 output, and shorten image-pickup cycles. An MIS type photoelectric conversion elements using an amorphous semiconductor material are connected with an electric power source for applying bias (Vs) for photoelectric conversion, an electric power (VREF) for resetting an 10 accumulated electric charge, and a setting point for applying zero bias (VGND) at the time of non-operation of the element through SW1. Emitted x-rays from an x-ray source, which is a first light source, come into collision against a phosphor after being transmitted 15 through an object body to be inspected which is not illustrated in drawings and then are absorbed in the phosphor to be converted to visible light rays. The visible light rays from the phosphor are radiated to the photoelectric conversion elements. Prior to 20 reading out of the x-ray image, an LED light source is lighted. SW2 and SW3 are switches for turning on the x-ray source and the LED light source, respectively. In this embodiment, there are a reading-out period and a non-reading-out period, and the x-ray source is 25 turned on during the reading-out period and the LED light source is turned on during the non-reading-out period.

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